



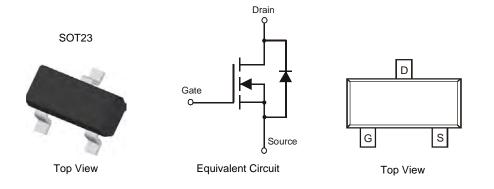
#### N-CHANNEL ENHANCEMENT MODE MOSFET

### **Features**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead, Halogen and Antimony Free, RoHS Compliant (Note 1)
- "Green" Device (Note 2)

### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)



#### Ordering Information (Note 3)

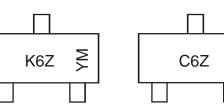
Part Number	Case	Packaging
MMBF170-7-F	SOT23	3000/Tape & Reel

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. No purposely added lead. Halogen and Antimony free.

2. Product manufactured with Date Code V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V9 are built with Non-Green Molding Compound and may contain Halogens or Sb<sub>2</sub>O<sub>3</sub> Fire Retardants.

3. For packaging details, go to our website at http://www.diodes.com.

## **Marking Information**



Date Code Key

Notes:

Year	1998	1999	2000	2001	2002	2003	2004		2011	2012	2013	2014	2015	2016	2017
Code	J	К	L	М	Ν	Р	R		Y	Z	А	В	С	D	E
Month	Jan	Fe	b I	Mar	Apr	Мау	Ju	n	Jul	Aug	Sep	Oc	t l	Nov	Dec
Code	1	2		3	4	5	6		7	8	9	0		Ν	D

Σ



# Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V <sub>DSS</sub>	60	V	
Drain-Gate Voltage $R_{GS} \le 1.0M\Omega$		V <sub>DGR</sub>	60	V	
Gate-Source Voltage	Continuous Pulsed	V <sub>GSS</sub>	±20 ±40	V	
Drain Current (Note 4)	Continuous Pulsed	۱ <sub>D</sub>	500 800	mA	

### Thermal Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

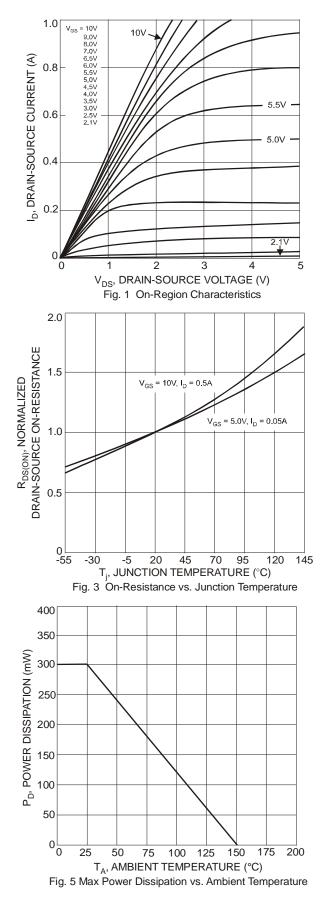
Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 4)	PD	300 1.80	m₩ mW/°C
Thermal Resistance, Junction to Ambient	$R_{ ext{ heta}JA}$	417	K/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	۵°

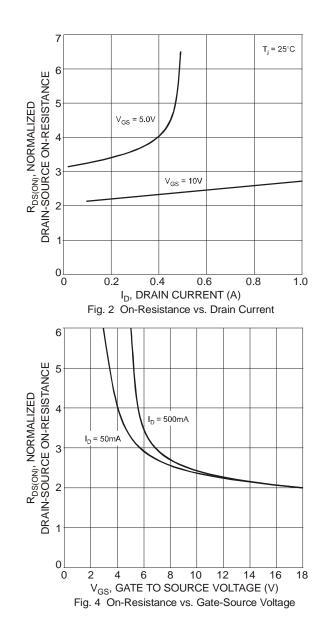
# Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)	Oymbol		тур	Max	Unit	rest condition
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	70	_	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 100μA
Zero Gate Voltage Drain Current	IDSS			1.0		$V_{DS} = 60V, V_{GS} = 0V$
Gate-Body Leakage	I <sub>GSS</sub>	_		±10	nA	$V_{GS} = \pm 15V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.8	2.1	3.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance				5.0	()	$V_{GS} = 10V, I_D = 200mA$
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)		—	5.3		$V_{GS} = 4.5V, I_D = 50mA$
Forward Transconductance	<b>g</b> fs	80	_		mS	V <sub>DS</sub> =10V, I <sub>D</sub> = 0.2A
DYNAMIC CHARACTERISTICS						·
Input Capacitance	C <sub>iss</sub>		22	40	pF	
Output Capacitance		_	11	30	pF	$V_{DS} = 10V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance	C <sub>rss</sub>		2.0	5.0	pF	
SWITCHING CHARACTERISTICS	•		•	•		•
Turn-On Time	t <sub>on</sub>			10	ns	$V_{DD} = 25V, I_D = 0.5A,$
Turn-Off Time	t <sub>off</sub>			10	ns	$V_{GS}$ = 10V, $R_{GEN}$ = 50 $\Omega$

Notes: 4. Device mounted on FR-4 PCB 1.0 x 0.75 x 0.062 inch pad layout as shown on Diodes, Inc. suggested pad layout AP02001, which can be found on our website at http://www.diodes.com. 5. Short duration pulse test used to minimize self-heating effect.

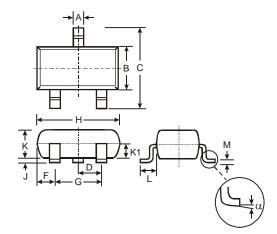






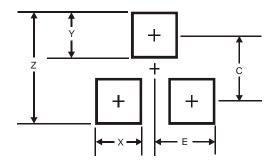


# Package Outline Dimensions



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
К	0.903	1.10	1.00				
K1	-	-	0.400				
L	0.45	0.61	0.55				
М	0.085	0.18	0.11				
α	0°	8°	-				
All Dimensions in mm							

# Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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